

September 2014

## FDMA86151L

# Single N-Channel PowerTrench® MOSFET

**100 V, 3.3 A, 88 m**Ω

## **Features**

- Max  $r_{DS(on)}$  = 88 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 3.3 A
- Max  $r_{DS(on)}$  = 132 m $\Omega$  at  $V_{GS}$  = 4.5 V,  $I_D$  = 2.7 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x2 mm
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

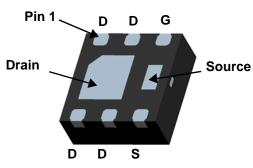
## **General Description**

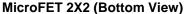
This device has been designed to provide maximum efficiency and thermal performance for synchronous buck converters. The low rDS(on) and gate charge provide excellent switching performance.

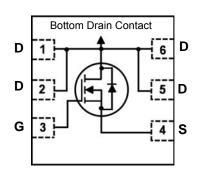
## **Application**

■ DC – DC Buck Converters









## MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

| Symbol                            | Parameter  |                        |             | Ratings | Units |
|-----------------------------------|--|------------------------|-------------|---------|-------|
| $V_{DS}$                          | Drain to Source Voltage                          |                        |             | 100     | V     |
| $V_{GS}$                          | Gate to Source Voltage                           |                        |             | ±20     | V     |
| 1                                 | Drain Curre -Continuous                          | T <sub>A</sub> = 25 °C | (Note 1a)   | 3.3     | ^     |
| ID                                | -Pulsed  |                        | (Note 3)    | 20      | A     |
| D                                 | Power Dissipation                                | T <sub>A</sub> = 25 °C | (Note 1a)   | 2.4     | W     |
| $P_{D}$                           | Power Dissipation                                | T <sub>A</sub> = 25 °C | (Note 1b)   | 0.9     | VV    |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range |                        | -55 to +150 | °C      |       |

## **Thermal Characteristics**

| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | (Note 1a) | 52  | °C/W |
|-----------------|---|-----------|-----|------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | (Note 1b) | 145 | C/VV |

## **Package Marking and Ordering Information**

| Device Marking | Device     | Package      | Reel Size | Tape Width | Quantity   |
|----------------|------------|--------------|-----------|------------|------------|
| 151            | FDMA86151L | MicroFET 2X2 | 7 "       | 8 mm       | 3000 units |

## Electrical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

| Symbol                                 | Parameter                                 | Test Conditions                                   | Min | Тур | Max | Units |
|--|---|---|-----|-----|-----|-------|
| Off Chara                              | acteristics                               |   |     |     |     |       |
| $BV_{DSS}$                             | Drain to Source Breakdown Voltage         | $I_D = 250 \mu A, V_{GS} = 0 V$                   | 100 |     |     | V     |
| $\frac{\Delta BV_{DSS}}{\Delta T_{J}}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 $\mu$ A, referenced to 25 °C          |     | 69  |     | mV/°C |
| I <sub>DSS</sub>                       | Zero Gate Voltage Drain Current           | V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V     |     |     | 1   | μА    |
| I <sub>GSS</sub>                       | Gate to Source Leakage Current            | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ |     |     | 100 | nA    |

## **On Characteristics**

| $V_{GS(th)}$                           | Gate to Source Threshold Voltage                            | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$               | 1.0 | 2.0 | 3.0 | V        |  |
|--|---|--|-----|-----|-----|----------|--|
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage<br>Temperature Coefficient | $I_D$ = 250 $\mu$ A, referenced to 25 °C           |     | -6  |     | mV/°C    |  |
|  |   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.3 A     |     | 60  | 88  |          |  |
| r                                      | Static Drain to Source On Resistance                        | $V_{GS} = 4.5 \text{ V}, I_D = 2.7 \text{ A}$      |     | 83  | 132 | 32<br>mΩ |  |
| r <sub>DS(on)</sub> Static Dra         | Static Brain to Source On Nesistance                        | $V_{GS}$ = 10 V, $I_{D}$ = 3.3 A, $T_{J}$ = 125 °C |     | 102 | 150 | 11122    |  |
| g <sub>FS</sub>                        | Forward Transconductance                                    | V <sub>DD</sub> = 5 V, I <sub>D</sub> = 3.3 A      |     | 8.6 |     | S        |  |

## **Dynamic Characteristics**

| C <sub>iss</sub> | Input Capacitance            | V - 50 V V - 0 V   |     | 322 | 450 | pF |
|------------------|------------------------------|--|-----|-----|-----|----|
| Coss             | Output Capacitance           | $V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$ |     | 55  | 80  | pF |
| C <sub>rss</sub> | Reverse Transfer Capacitance | 1 - 1 1/11/12  |     | 3   | 5   | pF |
| $R_q$            | Gate Resistance              |  | 0.1 | 1.9 | 3.8 | Ω  |

## **Switching Characteristics**

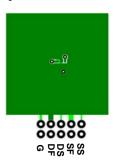
| $t_{d(on)}$         | Turn-On Delay Time            | ., -0,,,   | 5.6 | 12  | ns |
|---------------------|-------------------------------|--|-----|-----|----|
| t <sub>r</sub>      | Rise Time                     | $V_{DD} = 50V, I_D = 3.3 A,$ $V_{GS} = 10 V, R_{GEN} = 6 \Omega$   | 1.4 | 10  | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time           | V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω                     | 11  | 20  | ns |
| t <sub>f</sub>      | Fall Time                     |  | 1.6 | 10  | ns |
| $Q_{g(TOT)}$        | Total Gate Charge             | V <sub>GS</sub> = 0 V to 10 V                                      | 5.2 | 7.3 | nC |
| $Q_{g(TOT)}$        | Total Gate Charge             | $V_{GS} = 0 \text{ V to } 4.5 \text{ V}$ $V_{DD} = 50 \text{ V}$ , | 2.6 | 3.7 | nC |
| Q <sub>gs</sub>     | Gate to Source Charge         | I <sub>D</sub> = 3.3 A   | 1.1 |     | nC |
| Q <sub>qd</sub>     | Gate to Drain "Miller" Charge |  | 1.0 |     | nC |

## **Drain-Source Diode Characteristics**

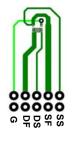
| $V_{SD}$        | Source to Drain Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_S = 3.3 \text{ A}$ (Note 2)                     |  | 0.8 | 1.2 | V  |
|-----------------|---------------------------------------|--|--|-----|-----|----|
| t <sub>rr</sub> | Reverse Recovery Time                 | I <sub>E</sub> = 3.3 A. di/dt = 100 A/us                                 |  | 33  | 53  | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge               | $T_{\rm F} = 3.3  \text{A},  \text{di/dt} = 100  \text{A/} \mu \text{s}$ |  | 25  | 40  | nC |

### NOTES

<sup>1.</sup>  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a. 52 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300  $\mu\text{s},$  Duty cycle < 2.0%.
- Pulsed Id limited by junction temperature, td<=10 μS, please refer to SOA curve for more details.</li>

## Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

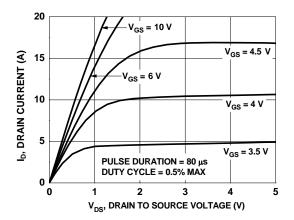


Figure 1. On-Region Characteristics

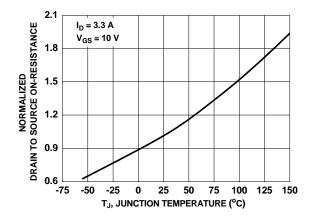


Figure 3. Normalized On-Resistance vs Junction Temperature

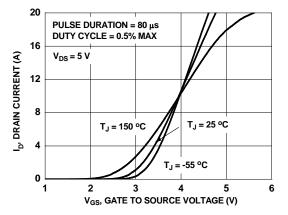


Figure 5. Transfer Characteristics

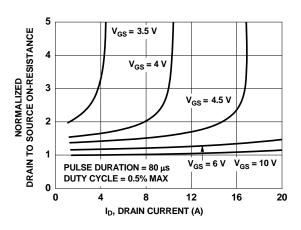


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

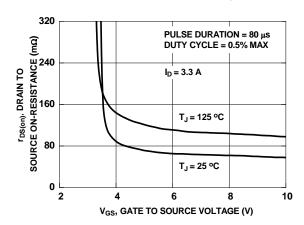


Figure 4. On-Resistance vs Gate to Source Voltage

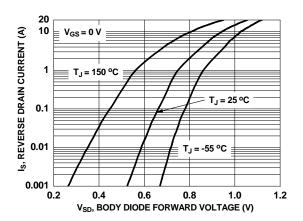


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## **Typical Characteristics** $T_J = 25^{\circ}C$ unless otherwise noted

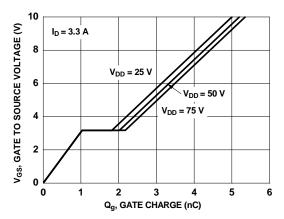


Figure 7. Gate Charge Characteristics

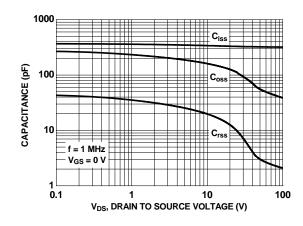


Figure 8. Capacitance vs Drain to Source Voltage

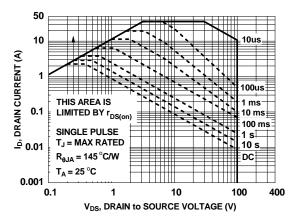


Figure 9. Forward Bias Safe Operating Area

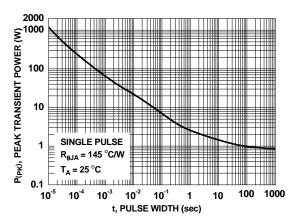


Figure 10. Single Pulse Maximum Power Dissipation

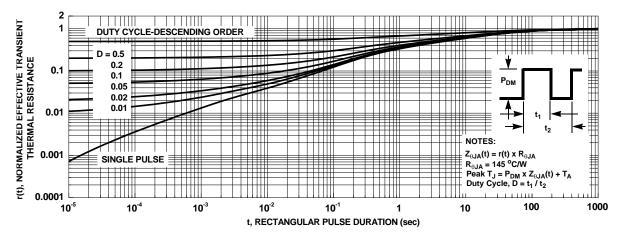
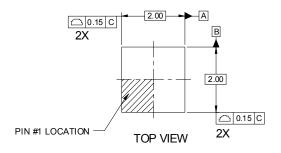
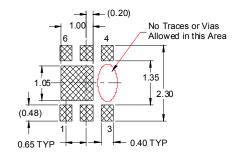


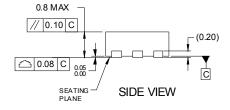
Figure 11. Single Pulse Junction-to-Ambient Transient Thermal Response Curve

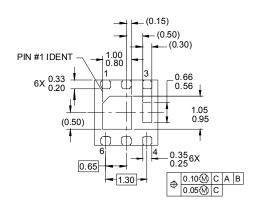
## **Dimensional Outline and Pad Layout**



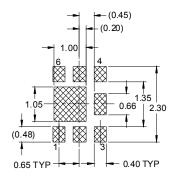


RECOMMENDED LAND PATTERN OPT 1









RECOMMENDED LAND PATTERN OPT 2

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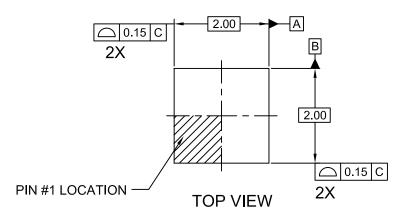
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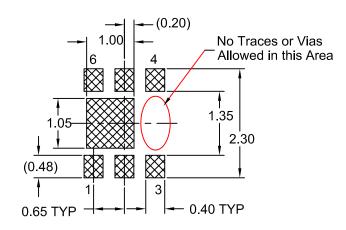
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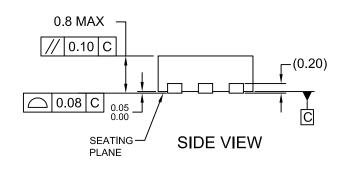
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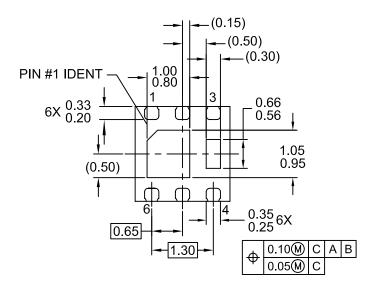
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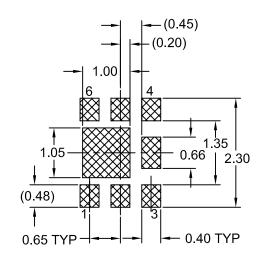




## RECOMMENDED LAND PATTERN OPT 1







**RECOMMENDED LAND PATTERN OPT 2** 

## NOTES:

A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003

**BOTTOM VIEW** 

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- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
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| Advance Information             | Formative / In Design | Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.   |
| Preliminary                     | First Production      | Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design. |
| No Identification Needed        | Full Production       | Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.   |
| Obsolete                        | Not In Production     | Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.  |

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